



Patent
Attorney's Docket No. 001425-104

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of)

Masahiko TANAKA et al.)

Application No.: 09/862,458)

Filed: May 23, 2001)

For: THIN-FILM DISPOSITION
APPARATUS)

Group Art Unit: 1763

Examiner: Karla A. Moore

Confirmation No.: 7476

#5A
2/11/03
KW

AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

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FEB 10 2003
TC 1700 MAIL ROOM

In response to the Official Action dated November 6, 2002, please amend the
above-identified patent application as follows:

IN THE SPECIFICATION:

Please replace paragraphs 25 and 54 as follows:

A₁
[0025] In the above-mentioned thin-film deposition apparatus according to the present invention, the above-mentioned plurality of holes through which the radicals pass are preferably formed so as to satisfy the condition $uL/D > 1$, where u is the gas flow rate inside these holes, L is the effective length of the holes (in the embodiments shown in Figures 2, 3 and 4, this length is equivalent to the thickness of dividing plate 24), and D is the gas interdiffusion coefficient (the gas interdiffusion coefficient of the precursor gas and the gas introduced in the plasma discharge space at the holes). In a thin-film deposition